

Schottky barrier diode

RB721Q-40

●Applications

High speed switching

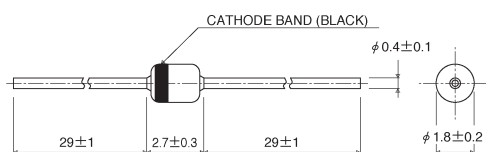
●Features

- 1) Glass-sealed envelope for high reliability. (MSD)
- 2) Small pitch enables insertion on PCBs.
- 3) Low reverse current and low forward voltage.

●Construction

Silicon epitaxial

●External dimensions (Units: mm)



ROHM : MSD
JEDEC : DO - 34

Product identification number "S2"
is stamped on body of main unit.

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	30	mA
Peak forward surge current*	I_{FSM}	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60 Hz for 1 ms

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	0.31	0.37	V	$I_F = 1\text{mA}$
Reverse current	I_R	—	0.06	0.5	μA	$V_R = 25\text{V}$
Capacitance between terminals	C_T	—	2.0	—	pF	$V_R = 1\text{V}$, $f = 1\text{MHz}$

* ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

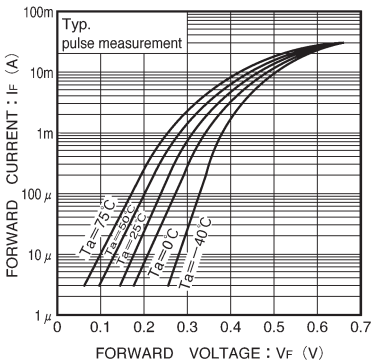


Fig. 1 Forward characteristics

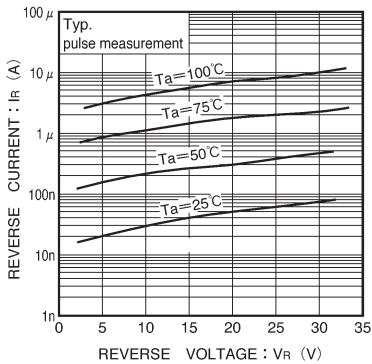


Fig. 2 Reverse characteristics

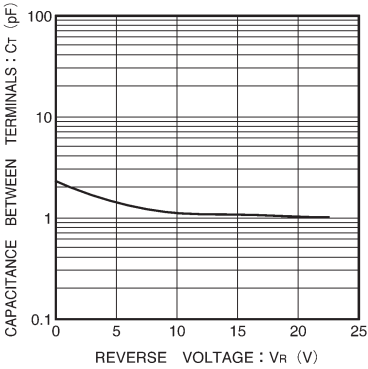


Fig. 3 Capacitance between terminals characteristics

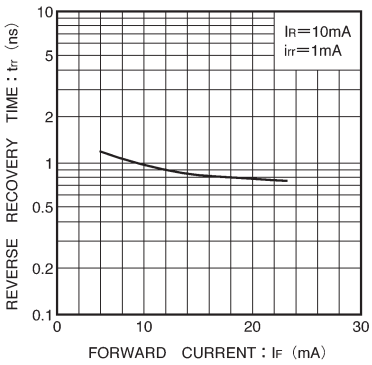


Fig. 4 Reverse recovery time characteristics

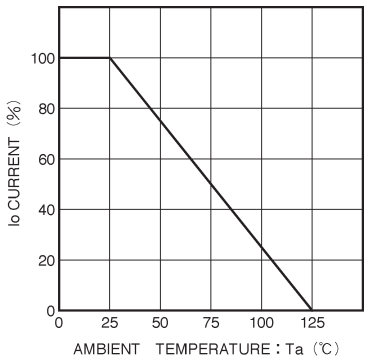


Fig. 5 Derating curve (mounting on glass epoxy PCBs)